650V GaN Power Transistor (FET)

Features

- Easy to use, compatible with standard gate drivers
- Low Q_{rr}, no free-wheeling diode required
- Excellent Q_g x $R_{DS(on)}$ product (FOM)
- Low switching loss
- RoHS compliant and Halogen-free

Product Summary

V_{DSS}	650	V
$R_{DS(on), typ}$	125	mΩ
$Q_{G, typ}$	22	nC
$Q_{RR, typ}$	55	nC

Applications

- Power adapters
- Telecom and datacom
- Automotive
- Servo motors
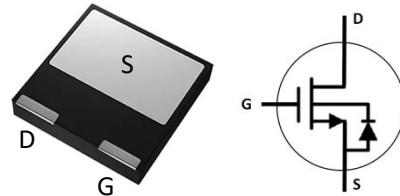
Packaging

Part Number	Package	Packaging	Base QTY
XG65T125HS1A	DFN 8*8mm	Tape and Reel	2500

Maximum ratings, at T_C=25 °C, unless otherwise specified

Symbol	Parameter		Limit Value	Unit
I_D	Continuous drain current @T_C=25°C		18	A
	Continuous drain current @T_C=100°C		11.5	A
I_{DM}	Pulsed drain current @T_C=25°C (pulse width: 10us)		100	A
	Pulsed drain current @T_C=150°C (pulse width: 10us)		70	A
V_{DSS}	Drain to source voltage (T_J = -55°C to 150°C)		650	V
V_{GSS}	Gate to source voltage		±20	V
P_D	Maximum power dissipation @T_C=25°C		67.5	W
T_C	Operating temperature	Case	-55 to 150	°C
T_J		Junction	-55 to 150	°C
T_S	Storage temperature		-55 to 150	°C
T_{CSOLD}	Soldering peak temperature		260	°C

Thermal Resistance

Symbol	Parameter	Typical	Unit
$R_{\Theta JC}$	Junction-to-case	1.85	°C/W
$R_{\Theta JA}$	Junction-to-ambient	80	°C/W

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Electrical Parameters, at T_J=25 °C, unless otherwise specified

Symbol	Min	Typ	Max	Unit	Test Conditions
Forward Device Characteristics					
$V_{DSS-MAX}$	650	-	-	V	V_{GS}=0V
BV_{DSS}	-	1700	-	V	V_{GS}=0V, I_{DSS}=250μA
$V_{GS(th)}$	-	1.62	-	V	V_{DS}=V_{GS}, I_D=500μA
$R_{DS(on)}$[a]	-	125	150	mΩ	V_{GS}=8V, I_D=4A, T_J=25°C
	-	250	-		V_{GS}=8V, I_D=4A, T_J=150°C
I_{DSS}	-	7	15	μA	V_{DS}=700V, V_{GS}=0V, T_J=25°C
	-	20	-	μA	V_{DS}=700V, V_{GS}=0V, T_J=150°C
I_{GSS}	-	-	150	nA	V_{GS}=20V
	-	-	-150	nA	V_{GS}=-20V
C_{ISS}	-	1470	-	pF	V_{GS}=0V, V_{DS}=650V, f=1MHz
C_{OSS}	-	55	-	pF	
C_{RSS}	-	1.5	-	pF	
$C_{O(er)}$	-	70	-	pF	V_{GS}=0V, V_{DS}=0 to 650V
$C_{O(tr)}$	-	120	-	pF	
Q_G	-	22	-	nC	V_{DS}=400V, V_{GS}=0V to 8V, I_D=10A
Q_{GS}	-	4.2	-		
Q_{GD}	-	3.6	-		
$t_{D(on)}$	-	30	-	nS	V_{DS}=400V, V_{GS}=0V to 12V, I_D=10A, R_G=34Ω
t_R	-	10	-		
$t_{D(off)}$	-	60	-		
t_F	-	9	-		
Reverse Device Characteristics					
V_{SD}	-	1.3	-	V	V_{GS}=0V, I_S=5A, T_J=25°C
	-	1.9	-		V_{GS}=0V, I_S=10A, T_J=25°C
	-	3	-		V_{GS}=0V, I_S=10A, T_J=150°C
t_{RR}	-	14	-	ns	I_S=10A, V_{GS}=0V, d_i/d_t=1000A/us, V_{DD}=400V
Q_{RR}	-	55	-	nC	

Notes:

a. Dynamic on-resistance; see Fig. 15 and 16 for test circuit and conditions

Circuit Implementation
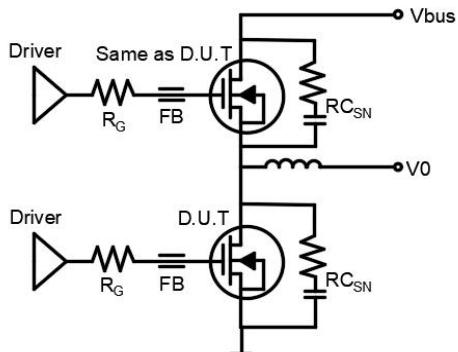
Recommended Drive Circuit

Recommended gate drive: (0 V, 12 V) with $R_{G(tot)} = 34\ \Omega$, where $R_{G(tot)} = R_G + R_{Driver}$

Gate Ferrite Bead (FB)	Gate Resistance1 (R_G)	RC Snubber (RC_{SN})
MMZ1608S301ATA00	33 Ω	47 pF + 15 Ω

Notes:

a.   RCsn should be placed as close as possible to the drain pin

b.   The layout and wiring of the drive circuit should be as short as possible

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Typical Characteristics, at T$_C$=25 °C, unless otherwise specified
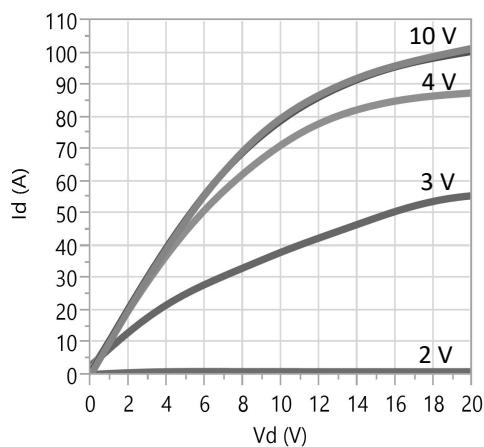
Figure 1. Typical Output Characteristics T$_J$=25°C

Parameter: V$_{GS}$
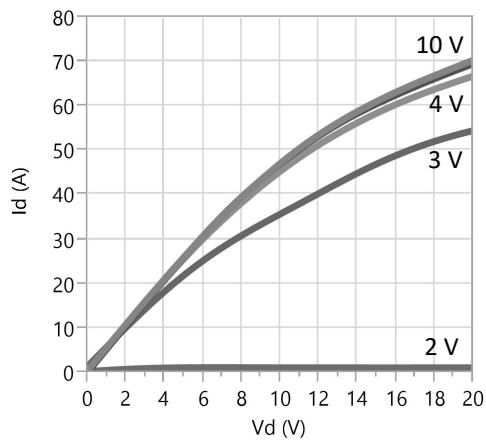
Figure 2. Typical Output Characteristics T$_J$=150°C

Parameter: V$_{GS}$
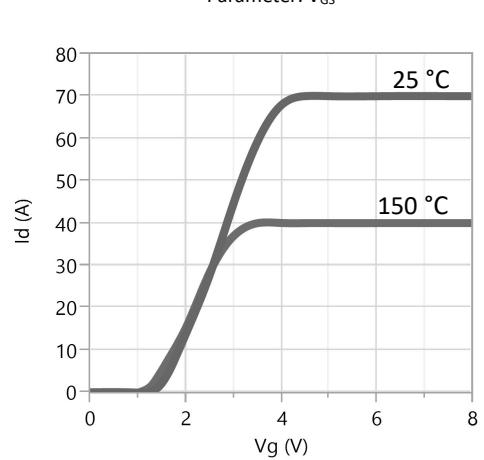
Figure 3. Typical Transfer Characteristics

V$_{DS}$=10V, Parameter: T$_J$
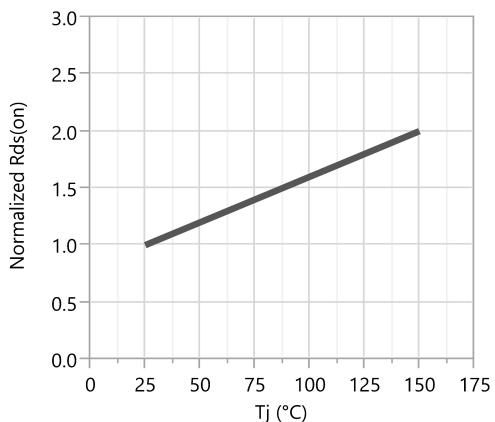
Figure 4. Normalized On-resistance

I$_D$=4A, V$_{GS}$=8V
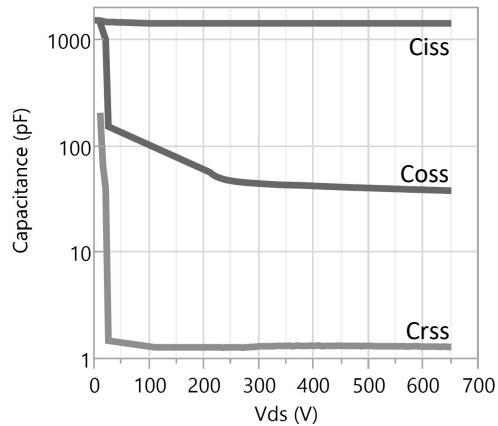
Figure 5. Typical Capacitance

V$_{GS}$=0V, f=1MHZ
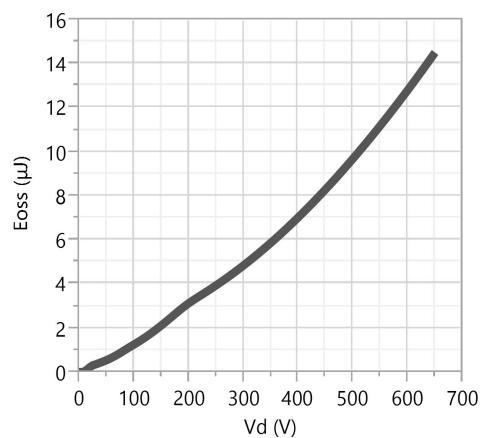
Figure 6. Typical Coss Stored Energy

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**Typical Characteristics, at T_C=25 °C, unless otherwise specified**
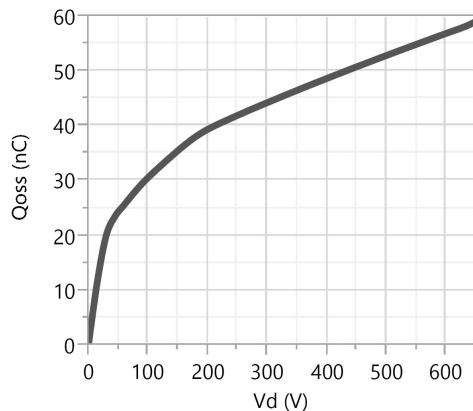
Figure 7. Typical Qoss
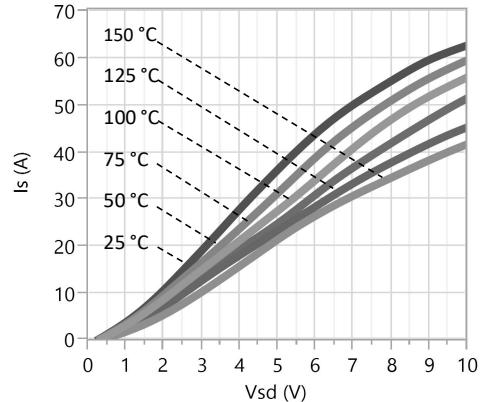
Figure 8. Forward Characteristic of Rev. Diode

I_s=f(V_S), Parameter T_J
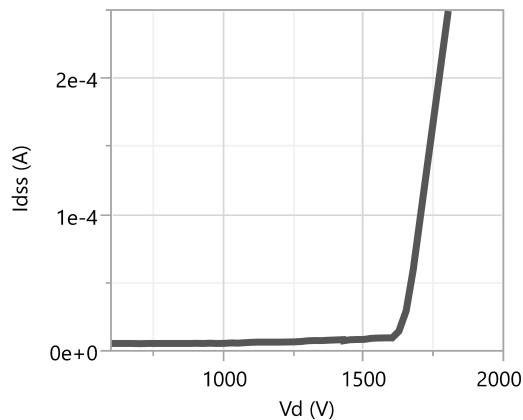
Figure 9. Drain-Source Breakdown Voltage
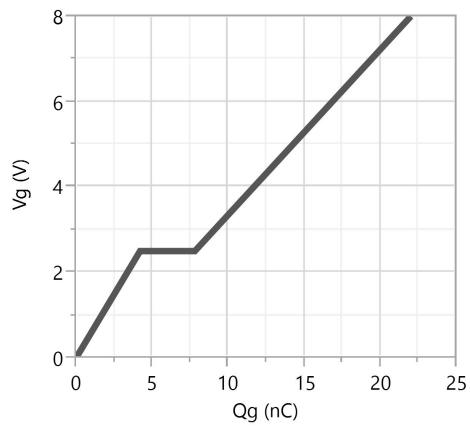
Figure 10. Typical Gate Charge

I_{DS}=10A, V_{DS}=400V
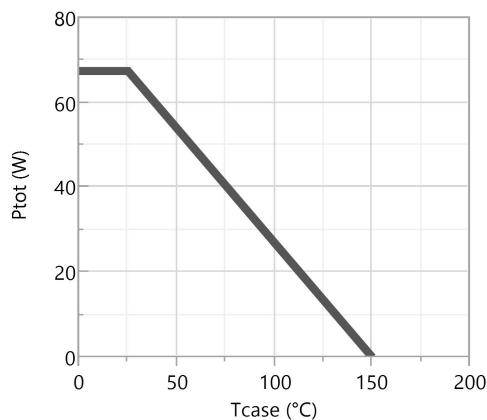
Figure 11. Power Dissipation
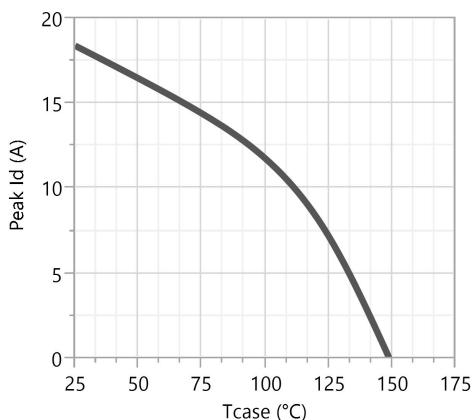
Figure 12. Current Derating

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Test Circuits and Waveforms
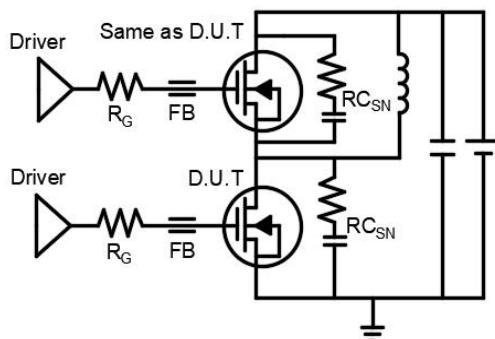
Figure 13. Switching Time Test Circuit
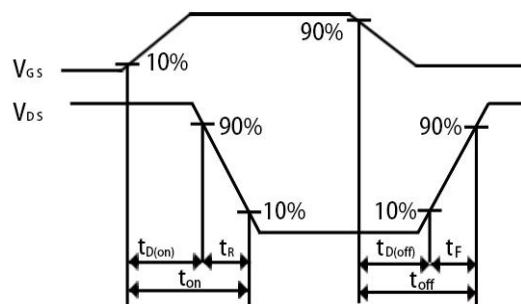

Figure 14. Switching Time Waveform
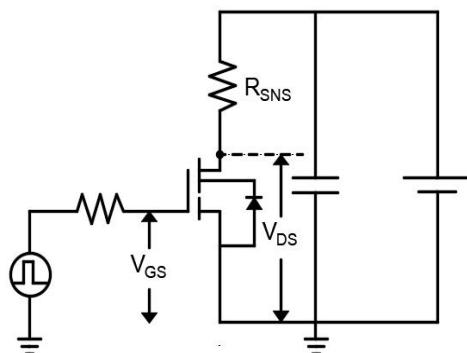

Figure 15. Dynamic $R_{DS(on)}$ Test Circuit
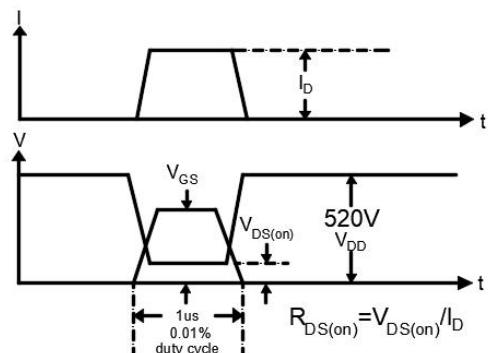
Figure 16. Dynamic $R_{DS(on)}$ Waveform
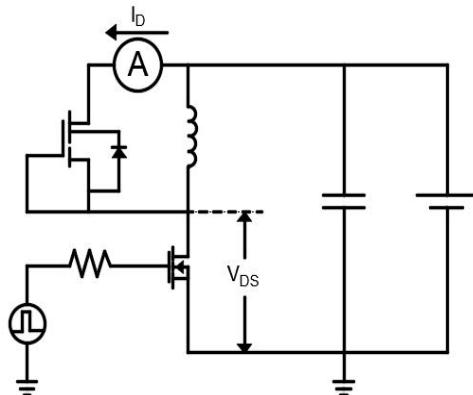
Figure 17. Diode Characteristic Test Circuit
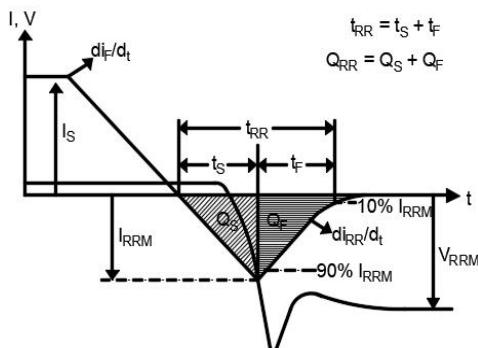
Figure 22. Diode Recovery Waveform

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Design Considerations

Fast switching GaN device can reduce power conversion losses, and thus enable high frequency operations. Certain PCB design rules and instructions, however, need to be followed to take full advantages of fast switching GaN devices.

Before evaluating Xinguan's GaN devices, please refer to the table below which provides some practical rules that should be followed during the evaluation.

When Evaluating Xinguan's GaN Devices:

| DO	DO NOT
Make sure the traces are as short as possible for both drive and power loops to minimize parasitic inductance	Using Xinguan's devices in GDS board layouts
Use the test tool with the shortest inductive loop, and make sure test points should be placed close enough	Use differential mode probe or probe ground clip with long wires
Minimize the lead length of TO packages when installing them to PCB	Use long traces in drive circuit, or long lead length of the devices

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Mechanical

TOP VIEW

SIDE VIEW

BOTTOM VIEW
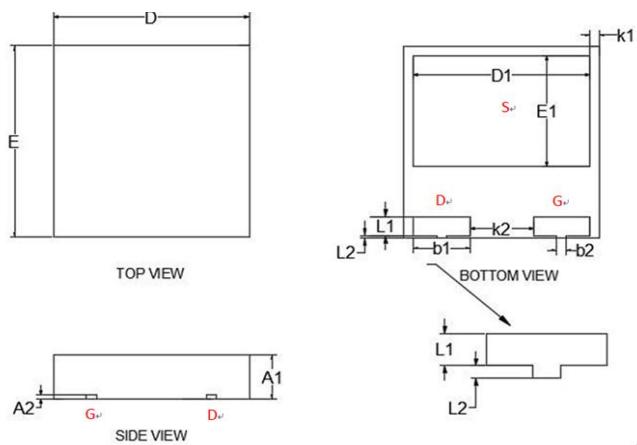
Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX
A1	1.825	1.850	1.875
A2	0.195	0.203	0.211
D	7.950	8.000	8.050
E	7.950	8.000	8.050
D1	7.150	7.200	7.250
E1	4.550	4.600	4.650
K1	0.375	0.400	0.425
K2	2.575	2.600	2.625
b1	2.275	2.300	2.325
b2	0.375	0.400	0.425
L1	0.775	0.800	0.825
L2	0.075	0.100	0.125

Package Outlines

Dimensions are show in millimeters

W	16.00+0.30/-0.30	T	0.30±0.05	Po	4.00±0.10	Ao	8.35±0.1	A1	
		F	7.50±0.10	P2	2.00±0.10	Bo	8.35±0.1	B1	
E	1.75±0.10	P	12.00±0.10	D0	Ø1.50+0.10/0	Ko	2.10±0.10	K1	
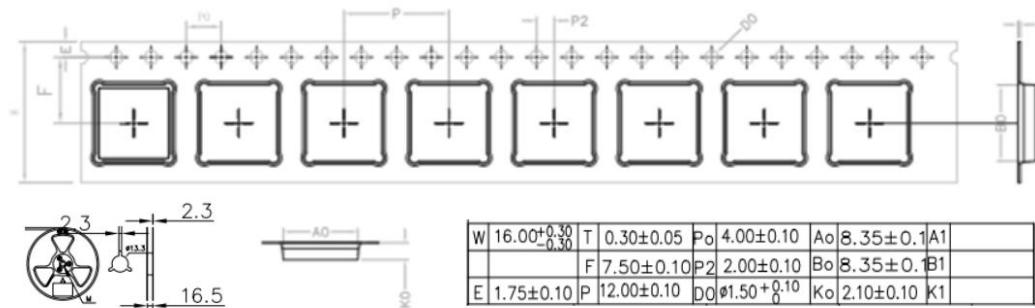
Revision History

Version	Date	Change(s)
1.0	5/1/2020	Release formal datasheet
1.1	6/1/2020	Added Package Outlines

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